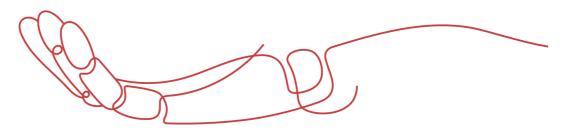


# **PRODUCT DATA SHEET**



To learn more about JGSEMI, please visit our website at



Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO\_questions@jgsemi.com.



**PZTA64** 

SOT-223 Plastic-Encapsulate Transistors

|   | SOT-223                 |
|---|-------------------------|
|   |                         |
| FEATURES  | 1. BASE                 |
| <ul><li>Low Voltage and High Current</li><li>High Current Gain Applications</li></ul> | 1 2 2<br>2. COLLECTOR 3 |
|   | 3. EMITTER              |

### MAXIMUM RATINGS (T<sub>a</sub>=25℃ unless otherwise noted)

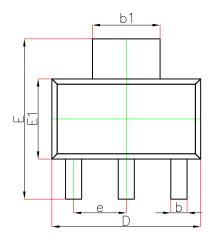
| Symbol                           | Parameter  | Value    | Unit |
|----------------------------------|--|----------|------|
| V <sub>CBO</sub>                 | Collector-Base Voltage                           | -30      | V    |
| V <sub>CEO</sub>                 | Collector-Emitter Voltage                        | -30      | V    |
| V <sub>EBO</sub>                 | Emitter-Base Voltage                             | -10      | V    |
| Ic                               | Collector Current                                | -500     | mA   |
| Pc                               | Collector Power Dissipation                      | 1        | W    |
| R <sub>0JA</sub>                 | Thermal Resistance From Junction To Ambient      | 125      | °C/W |
| T <sub>J</sub> ,T <sub>stg</sub> | Operation Junction and Storage Temperature Range | -55~+150 | ĉ    |

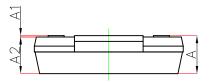
#### ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25<sup>°</sup>C unless otherwise specified)

| Parameter                            | Symbol                 | Test conditions                               | Min   | Тур | Max  | Unit |
|--------------------------------------|------------------------|---|-------|-----|------|------|
| Collector-emitter breakdown voltage  | V <sub>(BR)CES</sub>   | I <sub>C</sub> =-0.1mA,I <sub>B</sub> =0      | -30   |     |      | V    |
| Collector cut-off current            | I <sub>CBO</sub>       | V <sub>CB</sub> =-30V,I <sub>E</sub> =0       |       |     | -100 | nA   |
| Emitter cut-off current              | I <sub>EBO</sub>       | V <sub>EB</sub> =-10V, I <sub>C</sub> =0      |       |     | -100 | nA   |
| DC current gain                      | h <sub>FE(1)</sub> *   | V <sub>CE</sub> =-5V, I <sub>C</sub> =-10mA   | 10000 |     |      |      |
| DC current gain                      | h <sub>FE(2)</sub> *   | V <sub>CE</sub> =-5V, I <sub>C</sub> =-100mA  | 20000 |     |      |      |
| Collector-emitter saturation voltage | V <sub>CE(sat)</sub> * | I <sub>C</sub> =-100mA,I <sub>B</sub> =-0.1mA |       |     | -1.5 | V    |
| Base-emitter voltage                 | V <sub>BE</sub> *      | V <sub>CE</sub> =-5V, I <sub>C</sub> =-100mA  |       |     | -2   | V    |
| Transition frequency                 | f⊤                     | Vce=-5V,Ic=-10mA, f=100MHz                    | 125   |     |      | MHz  |

\*Pulse test: pulse width  $\leq$ 350µs, duty cycle $\leq$  2.0%.



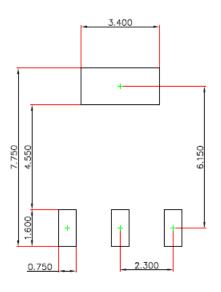




| -        | C<br>C         |   |
|----------|----------------|---|
|          |                |   |
|          |                |   |
| <b>i</b> | GAUGE<br>PLANE | ) |

| Symbol | Dimensions In Millimeters |       | Dimensions In Inches |       |
|--------|---------------------------|-------|----------------------|-------|
|        | Min.                      | Max.  | Min.                 | Max.  |
| А      |                           | 1.800 |                      | 0.071 |
| A1     | 0.020                     | 0.100 | 0.001                | 0.004 |
| A2     | 1.500                     | 1.700 | 0.059                | 0.067 |
| b      | 0.660                     | 0.840 | 0.026                | 0.033 |
| b1     | 2.900                     | 3.100 | 0.114                | 0.122 |
| С      | 0.230                     | 0.350 | 0.009                | 0.014 |
| D      | 6.300                     | 6.700 | 0.248                | 0.264 |
| Е      | 6.700                     | 7.300 | 0.264                | 0.287 |
| E1     | 3.300                     | 3.700 | 0.130                | 0.146 |
| е      | 2.300(BSC)                |       | 0.091(               | BSC)  |
| L      | 0.750                     |       | 0.030                |       |
| θ      | 0°                        | 10°   | 0°                   | 10°   |

### SOT-223 Suggested Pad Layout



#### Note:

1.Controlling dimension:in millimeters.

2.General tolerance:±0.050mm.

3. The pad layout is for reference purposes only.





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